Vincotech

F112R6A050SC

target datasheet

flowPACK 1 — **1200V/50A**

Features

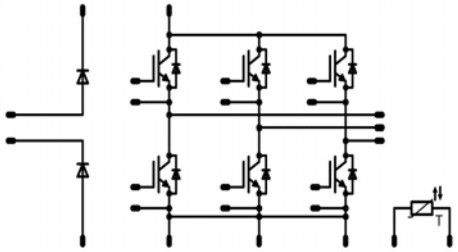
- Inverter, blocking diodes
- Very compact housing, easy to route
- IGBT4 technology

flow1 housing

Target Applications

- Power Regeneration

Schematic



Types

- 10-F112R6A050SC-M430E08
- 10-F112R6A050SC01-M430E18

Maximum Ratings

T_j=25°C, unless otherwise specified

Parameter	Symbol	Condition		Value	Unit
Blocking Diode					
Repetitive peak reverse voltage	V_{RRM}			1600	V
DC forward current	I_{FAV}	T_j=$T_j$max	T_h=80°C	50	A
Surge forward current	I_{FSM}	t_p=10ms	T_j=25°C	700	A
I2t-value	I^2t			2450	A^2s
Power dissipation per Diode	P_{tot}	T_j=$T_j$max	T_h=80°C	95	W
Maximum Junction Temperature	$T_j$max			150	°C
Inverter Transistor					
Collector-emitter break down voltage	V_{CE}			1200	V
DC collector current	I_C	T_j=$T_j$max	T_h=80°C	60	A
Repetitive peak collector current	I_{Cpulse}	t_p limited by $T_j$max		150	A
Turn off safe operating area		VCE ≤ 1200V, Tj ≤ Top max		150	A
Power dissipation per IGBT	P_{tot}	T_j=$T_j$max	T_h=80°C	100	W
Gate-emitter peak voltage	V_{GE}			±20	V
Short circuit ratings	t_{SC} V_{CC}	T_j≤150°C V_{GE}=15V		10 900	µs V
Maximum Junction Temperature	$T_j$max			175	°C

Maximum Ratings

T_j=25°C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Inverter Diode				
Peak Repetitive Reverse Voltage	V_{RRM}	T_j=25°C	1200	V
DC forward current	I_F	T_j=$T_j$max T_h=80°C	18	A
Repetitive peak forward current	I_{FRM}	t_p limited by $T_j$max	30	A
Power dissipation per Diode	P_{tot}	T_j=$T_j$max T_h=80°C	38	W
Maximum Junction Temperature	$T_j$max		175	°C
Thermal Properties				
Storage temperature	T_{stg}		-40…+125	°C
Operation temperature under switching condition	T_{op}		-40…+(Tjmax - 25)	°C
Insulation Properties				
Insulation voltage	V_{is}	t=2s DC voltage	4000	V
Creepage distance			min 12.7	mm
Clearance			min 12.7	mm
Comparative tracking index	CTI		>200	

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] or V_{GS} [V]	V_r [V] or V_{CE} [V] or V_{DS} [V]	I_C [A] or I_F [A] or I_D [A]	T_j	Min	Typ	Max	
Blocking Diode										
Forward voltage	V_F				50	Tj=25°C Tj=125°C		1.11 1.04	1.7	V
Threshold voltage (for power loss calc. only)	V_{to}				50	Tj=25°C Tj=125°C		0.91 0.78		V
Slope resistance (for power loss calc. only)	r_t				50	Tj=25°C Tj=125°C		4 5		mΩ
Reverse current	I_r			1600		Tj=25°C Tj=125°C			0.05 1.1	mA
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						0.74		K/W
Thermal resistance chip to heatsink per chip	R_{thJC}							0.49		
Inverter Transistor										
Gate emitter threshold voltage	$V_{GE(th)}$	$V_{CE}=V_{GE}$			0.0017	Tj=25°C Tj=150°C	5	5.8	6.5	V
Collector-emitter saturation voltage	$V_{CE(sat)}$		15		50	Tj=25°C Tj=150°C		1.86 2.3	2.3	V
Collector-emitter cut-off current incl. Diode	I_{CES}		0	1200		Tj=25°C Tj=150°C			0.02	mA
Gate-emitter leakage current	I_{GES}		20	0		Tj=25°C Tj=150°C			200	nA
Integrated Gate resistor	R_{gint}							4		Ω
Turn-on delay time	$t_{d(on)}$	Rgoff=8 Ω Rgon=8 Ω	±15	600	50	Tj=25°C Tj=150°C		104 100		ns
Rise time	t_r					Tj=25°C Tj=150°C		19 23.8		
Turn-off delay time	$t_{d(off)}$					Tj=25°C Tj=150°C		220 295		
Fall time	t_f					Tj=25°C Tj=150°C		78 118		
Turn-on energy loss per pulse	E_{on}					Tj=25°C Tj=150°C		2.86 4.5		mWs
Turn-off energy loss per pulse	E_{off}					Tj=25°C Tj=150°C		2.69 4.48		
Input capacitance	C_{ies}	f=1MHz	0	25		Tj=25°C		2770		pF
Output capacitance	C_{oss}							205		
Reverse transfer capacitance	C_{rss}							160		
Gate charge	Q_{Gate}		±15	960		Tj=25°C		290		nC
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						0.58		K/W
Thermal resistance chip to case per chip	R_{thJC}							0.38		
Inverter Diode										
Diode forward voltage	V_F				15	Tj=25°C Tj=150°C	1.35	1.90 1.91	2.35	V
Peak reverse recovery current	I_{RRM}	Rgon=8 Ω	±15	600	15	Tj=25°C Tj=150°C		16.06		A
Reverse recovery time	t_{rr}					Tj=25°C Tj=150°C		433.4		ns
Reverse recovered charge	Q_{rr}					Tj=25°C Tj=150°C		2.75		µC
Peak rate of fall of recovery current	di(rec)max /dt					Tj=25°C Tj=150°C		109		A/µs
Reverse recovered energy	Erec					Tj=25°C Tj=150°C		1.16		mWs
Thermal resistance chip to heatsink per chip	R_{thJH}	Thermal grease thickness≤50um λ = 1 W/mK						2.52		K/W
Thermal resistance chip to case per chip	R_{thJC}							tbd.		

Characteristic Values

Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] or V_{GS} [V]	V_r [V] or V_{CE} [V] or V_{DS} [V]	I_C [A] or I_F [A] or I_D [A]	T_j	Min	Typ	Max	
Thermistor										
Rated resistance	R					Tj=25°C		22000		Ω
Deviation of R100	ΔR/R	R100=1486 Ω				Tc=100°C	-5		5	%
Power dissipation	P					Tc=100°C		200		mW
Power dissipation constant						Tj=25°C		2		mW/K
B-value	$B_{(25/50)}$	Tol. ±3%				Tj=25°C		3950		K
B-value	$B_{(25/100)}$	Tol. ±3%				Tj=25°C		3996		K
Vincotech NTC Reference						Tj=25°C			B	
Module Properties										
Thermal resistance, case to heatsink	R_{thCH}							tbd.		K/W
Module stray inductance	L_{sCE}							5		nH
Chip module lead resistance, terminals -chip	$R_{cc'1+EE'}$							tbd.		mΩ
Mounting torque	M						3.8	4	4.2	Nm
Terminal connection torque	M						6.7	7	7.4	Nm
Weight	G							tbd.		g

Ordering Code and Marking - Outline - Pinout

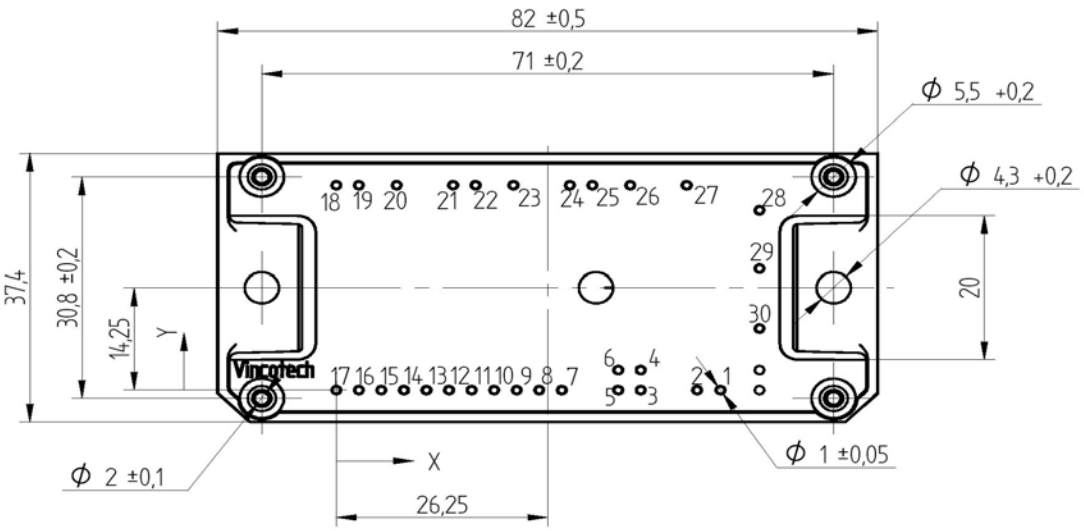
Ordering Code & Marking

Version	Ordering Code	in DataMatrix as	in packaging barcode as
12mm housing	10-F112R6A050SC-M430E08	M430-E08	M430-E08
12mm housing, without thermistor	10-F112R6A050SC01-M430E18	M430-E18	M430-E18

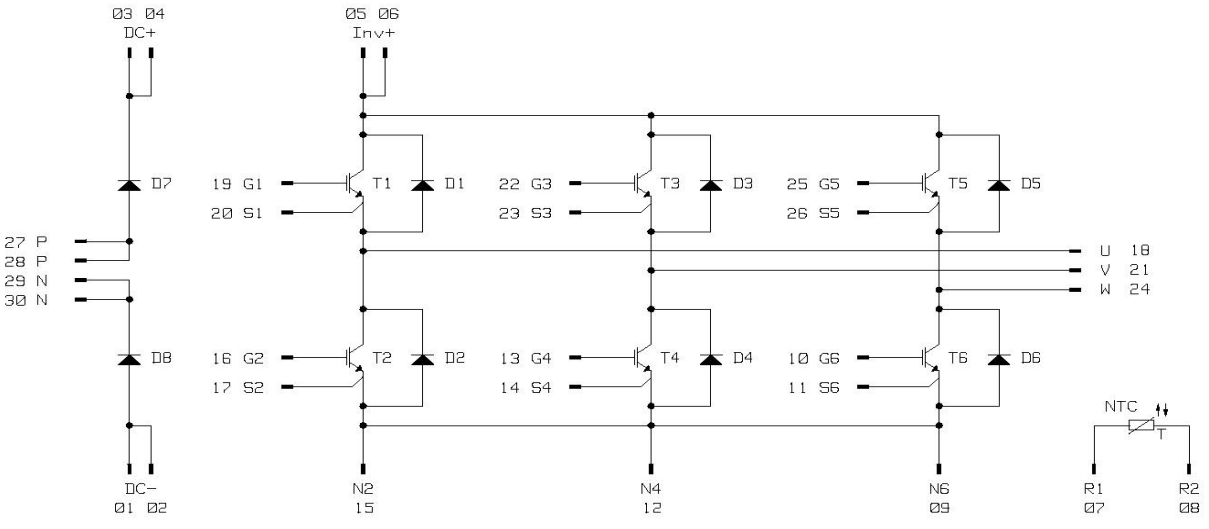
Outline

Pin table		
Pin	X	Y
1	47,7	0
2	44,8	0
3	37,8	0
4	37,8	2,8
5	35	0
6	35	2,8
7	28	0
8	25,2	0
9	22,4	0
10	19,6	0
11	16,8	0
12	14	0
13	11,2	0
14	8,4	0
15	5,6	0
16	2,8	0
17	0	0
18	0	28,5
19	2,8	28,5
20	7,5	28,5
21	14,5	28,5
22	17,3	28,5
23	22	28,5
24	29	28,5
25	31,8	28,5
26	36,5	28,5
27	43,5	28,5
28	52,55	25

Pin table		
Pin	X	Y
29	52,55	16,9
30	52,55	8,6



Pinout



PRODUCT STATUS DEFINITIONS

Datasheet Status	Product Status	Definition
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